

C' 21 a second interconnect selectively provided on the second interlayer  
22 insulating film and electrically connected to the first interconnect through a second  
23 contact hole formed in the second interlayer insulating film; and  
24 a passivation layer provided so as to cover the second interconnect.

---

1 30. (Amended) A semiconductor device, comprising:

2 a capacitor provided on a supporting substrate having an integrated  
3 circuit thereon and including a lower electrode, a dielectric film, and an upper  
4 electrode, said dielectric film including a remnant polarization of approximately 10  
5  $\mu\text{C}/\text{cm}^2$ ;

6 a first interlayer insulating film provided so as to directly cover the  
7 capacitor;

8 a first interconnect selectively provided on the first interlayer  
9 insulating film and electrically connected to the integrated circuit and the capacitor  
10 through a first contact hole formed in the first interlayer insulating film;

C2 11 a second interlayer insulating film having a tensile stress provided so  
12 as to directly cover the first interconnect and the first interlayer insulating film;

13 a second interconnect selectively provided on the second interlayer  
14 insulating film and electrically connected to the first interconnect through a second  
15 contact hole formed in the second interlayer insulating film; and

16 a passivation layer provided so as to cover the second interconnect.

31. (Amended) A semiconductor device, comprising:

a capacitor provided on a supporting substrate having an integrated  
circuit thereon and including a lower electrode, a dielectric film, and an upper  
electrode, said dielectric film including a remnant polarization of at least 10  
 $\mu\text{C}/\text{cm}^2$ ;

a first interlayer insulating film provided so as to directly cover the  
capacitor;

C2 a first interconnect selectively provided on the first interlayer insulating film and electrically connected to the integrated circuit and the capacitor through a first contact hole formed in the first interlayer insulating film;

a second interlayer insulating film having a tensile stress provided so as to directly cover the first interconnect and the first interlayer insulating film;

a second interconnect selectively provided on the second interlayer insulating film and electrically connected to the first interconnect through a second contact hole formed in the second interlayer insulating film; and

a passivation layer provided so as to cover the second interconnect.

---

Please cancel claim 2. ✓

Please add claim 32.

---

32 (Newly Added) A semiconductor device, comprising:

C3 1 a capacitor provided on a supporting substrate having an integrated  
2 circuit thereon and including a lower electrode, a dielectric film, and an upper  
3 electrode;  
4

5 a first interlayer insulating film provided so as to directly cover the  
6 capacitor, the first interlayer insulating film having a tensile stress;

7 a first interconnect selectively provided on the first interlayer  
8 insulating film and electrically connected to the integrated circuit and the capacitor  
9 through a first contact hole formed in the first interlayer insulating film;

10 a second interlayer insulating film having a tensile stress provided so  
11 as to directly cover the first interconnect and the first interlayer insulating film;

12 a second interconnect selectively provided on the second interlayer  
13 insulating film and electrically connected to the first interconnect through a second  
14 contact hole formed in the second interlayer insulating film; and

15

a passivation layer provided so as to cover the second interconnect.

---